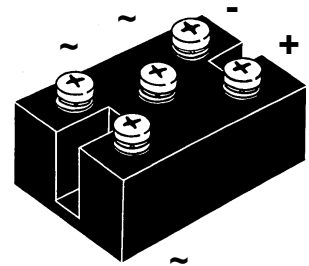
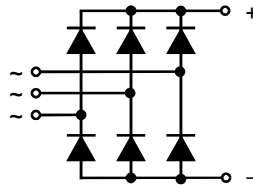


Three Phase Rectifier Bridge

$I_{dAVM} = 166 \text{ A}$
 $V_{RRM} = 1200-1800 \text{ V}$

V_{RSM}	V_{RRM}	Type
V	V	
1200	1200	VUO 125-12NO7
1400	1400	VUO 125-14NO7
1600	1600	VUO 125-16NO7
1800	1800	VUO 125-18NO7*

* delivery time on request



Symbol	Test Conditions	Maximum Ratings
I_{dAVM}	$T_C = 85^\circ\text{C}$, module	166 A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	t = 10 ms (50 Hz), sine 1800 A
		t = 8.3 ms (60 Hz), sine 1950 A
I^2t	$T_{VJ} = T_{VJM}$; $V_R = 0$	t = 10 ms (50 Hz), sine 1600 A
		t = 8.3 ms (60 Hz), sine 1800 A
I^2t	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	t = 10 ms (50 Hz), sine 16200 A ² s
		t = 8.3 ms (60 Hz), sine 16000 A ² s
T_{VJ}	T_{VJM}	-40...+150 °C
		150 °C
T_{stg}		-40...+150 °C
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	t = 1 min 2500 V~
		t = 1 s 3000 V~
M_d	Mounting torque (M5)	5 ± 15 % Nm
		44 ± 15 % lb.in.
Weight	typ.	Terminal connection torque (M5)
		5 ± 15 % Nm
		44 ± 15 % lb.in.

Features

- Package with screw terminals
- Isolation voltage 3000 V~
- Planar passivated chips
- Blocking voltage up to 1800 V
- Low forward voltage drop
- UL registered E 72873

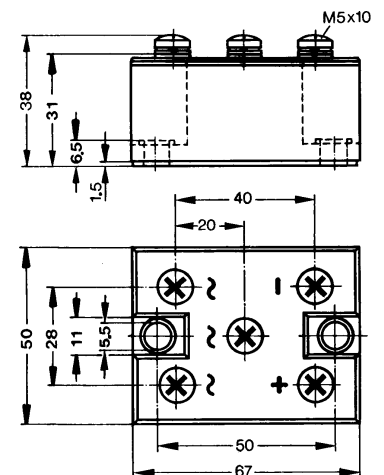
Applications

- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

Dimensions in mm (1 mm = 0.0394")



Symbol	Test Conditions	Characteristic Values
I_R	$V_R = V_{RRM}$; $V_R = V_{RRM}$	$T_{VJ} = 25^\circ\text{C}$ ≤ 0.3 mA
		$T_{VJ} = T_{VJM}$ ≤ 8.0 mA
V_F	$I_F = 150 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$	≤ 1.3 V
V_{T0}	For power-loss calculations only	0.8 V
r_T		3 mΩ
R_{thJC}	per diode per module	0.83 K/W
		0.138 K/W
R_{thJH}	per diode per module	1.13 K/W
		0.188 K/W

Data according to IEC 60747 and refer to a single diode unless otherwise stated. IXYS reserves the right to change limits, test conditions and dimensions.

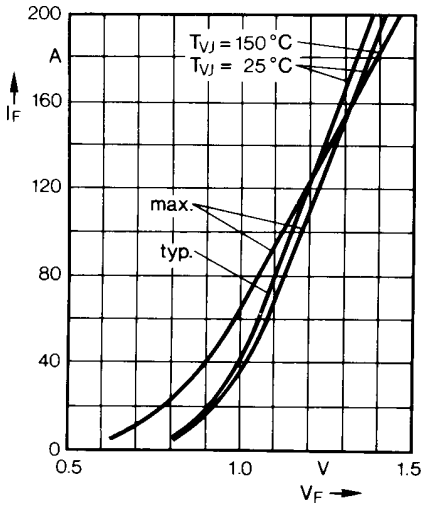


Fig. 1 Forward current versus voltage drop per diode

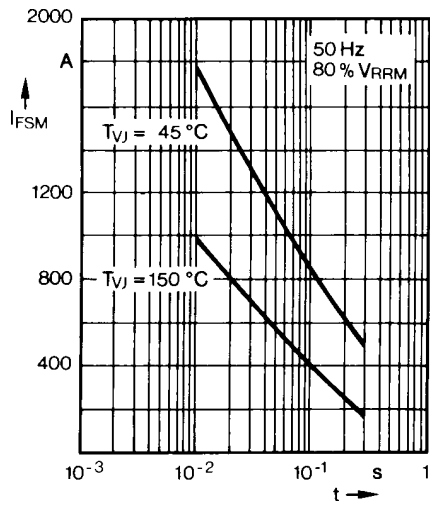


Fig. 2 Surge overload current per diode
 I_{FSM} : Crest value. t : duration

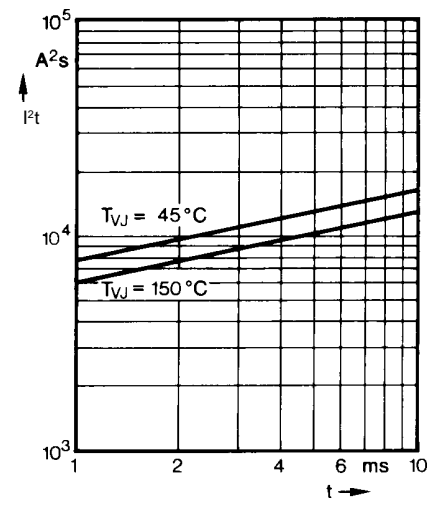


Fig. 3 I^2t versus time (1-10 ms) per diode

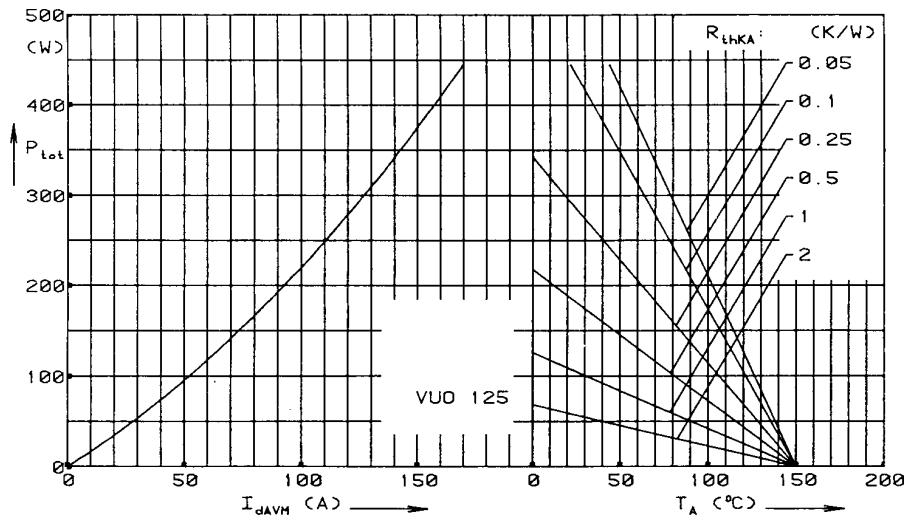


Fig. 4 Power dissipation versus direct output current and ambient temperature

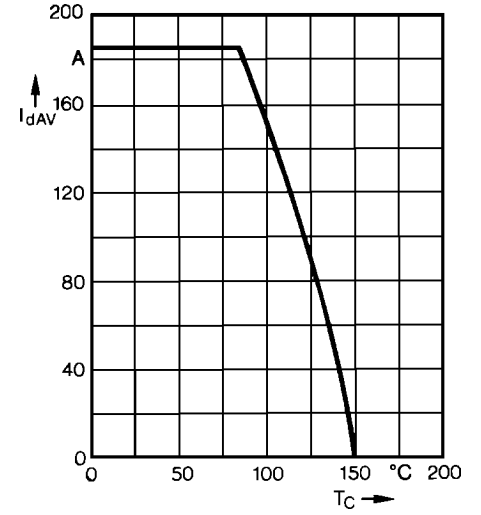


Fig. 5 Maximum forward current at case temperature

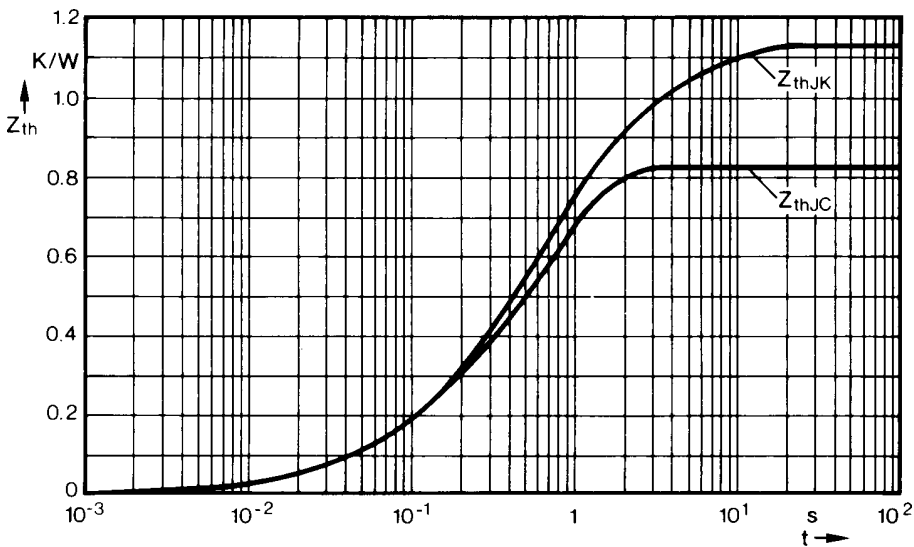


Fig. 6 Transient thermal impedance per diode

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.014	0.011
2	0.067	0.094
3	0.139	0.28
4	0.61	0.7

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.014	0.011
2	0.067	0.094
3	0.139	0.28
4	0.61	0.7
5	0.3	4.2